

ABSTRACT

An increased proportion of light projected from a nitride semiconductor light emitting diode enters the area within a specified angle.

The nitride semiconductor light emitting diode is provided with an active layer 32 consisting of a nitride semiconductor, and a light projecting face 21. A reflecting mirror 38 is formed only on a side of the active layer 32 opposite the light projecting face 21. The reflecting mirror 38 is formed at a location from the center of the active layer 32 approximately $(k \cdot \lambda/2 + \lambda/4)/n$ (where λ is the wavelength of light projected from the active layer 32, n is the mean refractive index of an area between the active layer 32 and the reflecting mirror 38, and k is an integer). This light emitting diode allows directivity to be increased sufficiently, and the coupling efficiency thereof with optical fiber consisting of POF or the like can be improved.